

# Magnetic Memory Devices Based On 4d And 5d Transition Metal Perovskites

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## The Invention

Magnetic switching devices, including magnetic memory devices, are provided. The devices use high-quality crystalline films of 4d or 5d transition metal perovskite having a strong spin-orbit coupling (SOC) to produce spin-orbit torque in adjacent ferromagnetic materials via a strong spin-Hall effect. Spin-orbit torque can be generated by the devices with a high efficiency, even at or near room temperature.

### Additional Information

### For More Information About the Inventors

<u>Chang-Beom Eom</u>

#### **Tech Fields**

- Information Technology : Hardware
- Materials & Chemicals : Composites

For current licensing status, please contact Michael Carey at mcarey@warf.org or 608-960-9867

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